

isc Silicon NPN Power Transistor

BD743A

DESCRIPTION

- · Collector-Emitter Breakdown Voltage-
 - : V_{(BR)CEO}= 60V(Min)
- · Collector Power Dissipation-
 - : P_C= 90W@ I_C= 25℃
- 15A Continuous Collector Current
- · Complement to Type BD744A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

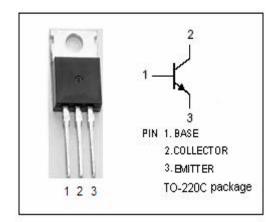
 Designed for use in general purpose power amplifier and switching applications.

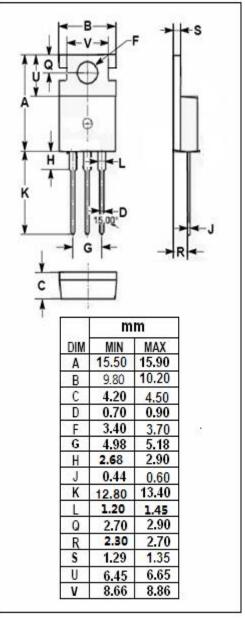
ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{CBO}	Collector-Base Voltage	70	V	
V _{CEO}	Collector-Emitter Voltage	60	V	
V _{EBO}	Emitter-Base Voltage	5	V	
Ic	Collector Current-Continuous	15	Α	
I _{CM}	Collector Current-Peak	20	А	
I _B	Base Current-Continuous	5	Α	
Pc	Collector Power Dissipation @ T _a =25°C	2	W	
	Collector Power Dissipation @ T _c =25°C	90		
TJ	Junction Temperature	150	$^{\circ}$	
T _{stg}	Storage Temperature Range	-65~150	$^{\circ}$	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT	
R _{th j-c}	Thermal Resistance, Junction to Case		°C/W	
R _{th j-a}	R _{th j-a} Thermal Resistance, Junction to Ambient		°C/W	





isc website: www.iscsemi.com



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ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 30mA; I _B = 0	60		V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 0.5A		1.0	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	Ic= 15A; I _B = 5A		3.0	V
V _{BE(on)-1}	Base-Emitter On Voltage	Ic= 5A ; V _{CE} = 4V		1.0	V
V _{BE(on)-2}	Base-Emitter On Voltage	Ic= 15A ; V _{CE} = 4V		3.0	V
І _{СВО}	Collector Cutoff Current	V _{CB} = 70V; I _E = 0		0.1	- mA
		V _{CB} = 70V; I _E = 0; T _C = 125℃		5.0	
I _{CEO}	Collector Cutoff Current	V _{CE} = 30V; I _B = 0		0.1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0		0.5	mA
h _{FE-1}	DC Current Gain	I _C = 1A; V _{CE} = 4V	40		
h _{FE-2}	DC Current Gain	I _C = 5A ; V _{CE} = 4V	20	150	
h _{FE-3}	DC Current Gain	I _C = 15A ; V _{CE} = 4V	5		

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